NSN 5961-01-005-9531

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-005-9531 **Inclosure Material:** Metal and glass **Overall Length:** Between 0.190 inches and 0.210 inches **Terminal Length:** 0.500 inches **Overall Diameter:** Between 0.209 inches and 0.230 inches **Function For Which Designed:** Phototransistor **Internal Configuration:** Point contact **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Gallium arsenide Voltage Rating In Volts Per Characteristic: 2.0 reverse voltage, dc **Current Rating Per Characteristic:** 200.00 milliamperes source cutoff current preset **Power Rating Per Characteristic:** 6.0 milliwatts any acceptable preset **Maximum Operating Tempurature Per Measurement Point:** 80.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pn **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Yes - demil/mli

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